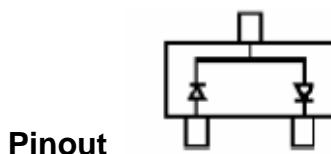
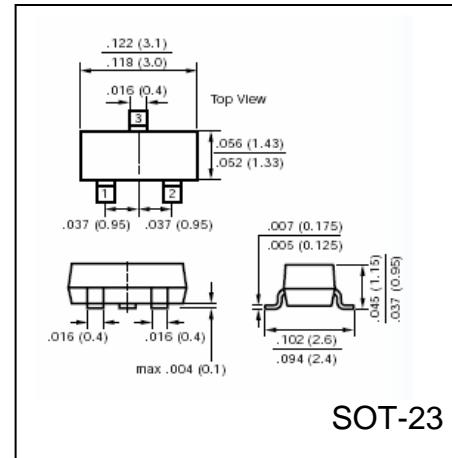


MEI**SURFACE MOUNT DUAL SWITCHING DIODE****BAW56**VOLTAGE RANGE
CURRENT100 Volts
150 mA**FEATURES**

- Fast Switching speed
- Low turn on Voltage
- General purpose switching applications
- High Conductance

MECHANICAL DATA

- Case: Transfer molded plastic, SOT-23
- Terminals: solderable per MIL-STD-202E Method 208C
- Pinout: See diagram
- Weight: 0.00028 ounce, 0.008gram

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

- Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOLS		UNIT
Non-Repetitive Peak Reverse Voltage	V_R	100	Volt
Maximum Repetitive Peak Reverse Voltage	V_{RM}	75	Volts
Forward Continuous Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Aurge Current @ $T = 1.0\mu\text{s}$ $T = 1.0\text{S}$	I_{FSM}	2.0 1.0	Amps
Maximum Forward Voltage @ 1.0mA 10mA 50mA 150mA	V_F	0.715 0.855 1.0 1.25	Volts
Maximum Leakage Current, (Note 1) @ $V_R = 75\text{V}$ $V_R = 75\text{V}, T_j = 150^\circ\text{C}$ $V_R = 25\text{V}, T_j = 150^\circ\text{C}$	I_R	2.5 50 30	μA
Maximum Reverse Recovery Time $I_F = 10\text{mA}, I_R = 10\text{mA}, I_{RR} = 1\text{mA}, R_L = 100\Omega$	t_{rr}	4	nS
Power dissipation (Note 1)	P_{TOT}	350	mW
Typical Junction Capacitance , $V_F = 1\text{V}, f = 1\text{MHz}$	C_J	2.0	pF
Typical Thermal Resistance	R_{QJA}	355	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_j	(-55 to +150)	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	(-55 to +150)	$^\circ\text{C}$

Notes:

1. Short duration pulse test used

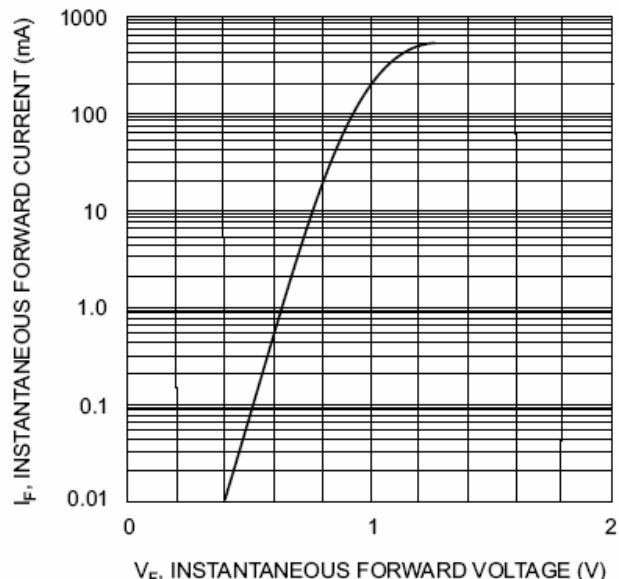
RATINGS AND CHARACTERISTIC CURVES BAW56

Fig. 1 Forward Characteristics

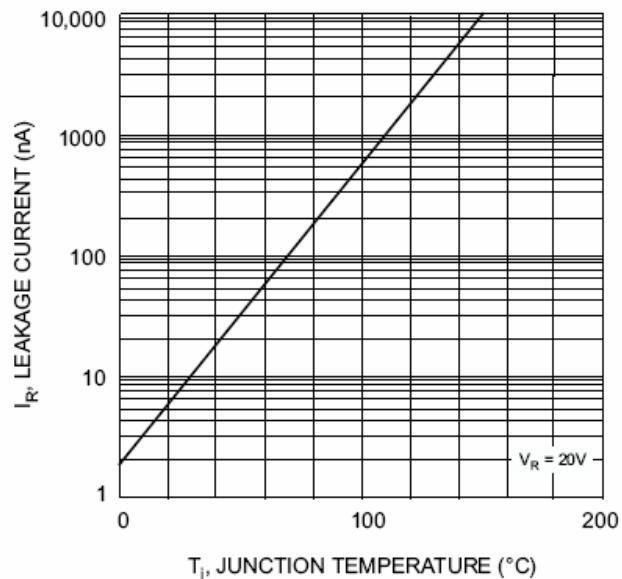


Fig. 2 Leakage Current vs Junction Temperature